

PSMN2R0-60ES

N-channel 60 V 2.2 mΩ standard level MOSFET in I2PAK Rev. 02 — 19 April 2011 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	60	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2		-	-	338	W
Tj	junction temperature			-55	-	175	°C
Static char	racteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$	[2]	-	1.8	2.2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \underline{\text{Figure 12}};$ $\text{see } \underline{\text{Figure 13}}$		-	3	3.5	mΩ
Dynamic c	haracteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A};$		-	32	-	nC
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>		-	137	-	nC
Avalanche	ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω; Unclamped		-	-	913	mJ



- [1] Continuous current limited by package.
- [2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT226 (I2PAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R0-60ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

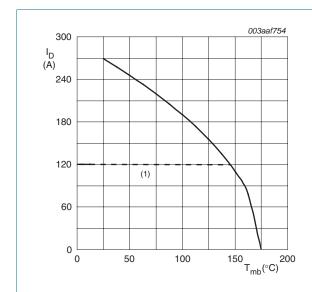
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		, ,				
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1]	-	120	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1]	-	120	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3		-	1135	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	338	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode					
Is	source current	T _{mb} = 25 °C	<u>[1]</u>	-	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1135	Α
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \le 60$ V; R_{GS} = 50 Ω ; Unclamped		-	913	mJ

[1] Continuous current limited by package



 $V_{\it GS} \geq$ 10 V(1) Capped at 120 A due to package

Fig 1. Continuous drain current as a function of mounting base temperature.

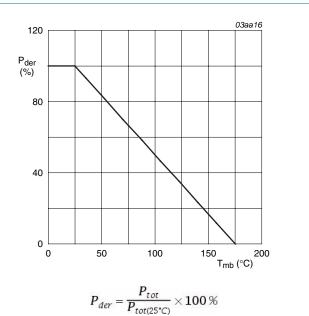


Fig 2. Normalized total power dissipation as a function of mounting base temperature

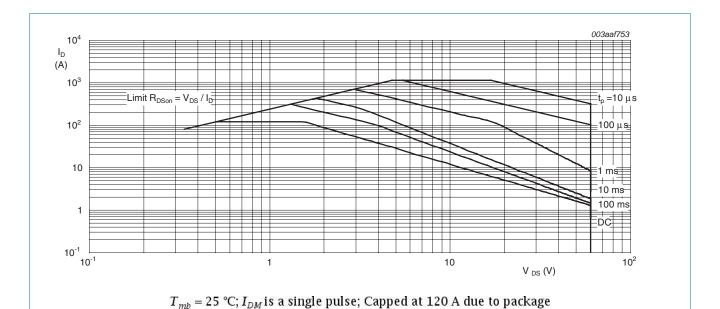
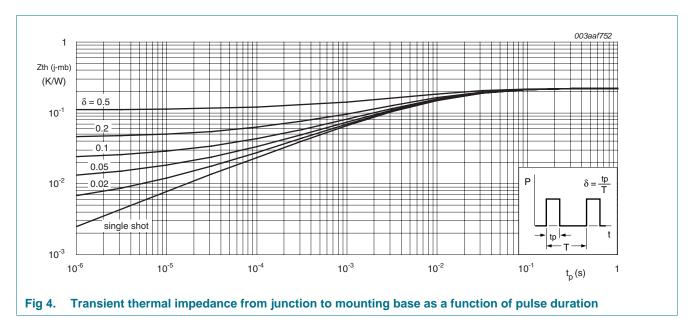


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W



6. Characteristics

Table 6 Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.03	10	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	[1] _	1.8	2.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	4.3	5.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	3	3.5	mΩ
R_G	gate resistance	f = 1 MHz	-	0.9	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 75 \text{ A}$; $V_{DS} = 30 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	137	-	nC
		$I_D = 0$ A; $V_{DS} = 0$ V; $V_{GS} = 10$ V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	129	-	nC
Q_{GS}	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V}$	-	48	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 75 \text{ A}$; $V_{DS} = 30 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	29	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	19	-	nC
Q_{GD}	gate-drain charge		-	32	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 30 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	5.7	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9997	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	1210	-	pF
C _{rss}	reverse transfer capacitance		-	594	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_L = 0.4 Ω ; V_{GS} = 10 V;	-	42	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega; I_D = 75 A$	-	56	-	ns
t _{d(off)}	turn-off delay time		-	115	-	ns
t _f	fall time		-	49	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	in diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$; $V_{DS} = 30 \text{ V}$	-	57	-	ns
Q _r	recovered charge	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$; $V_{DS} = 30 \text{ V}$	-	80	-	nC

[1] Measured 3 mm from package.

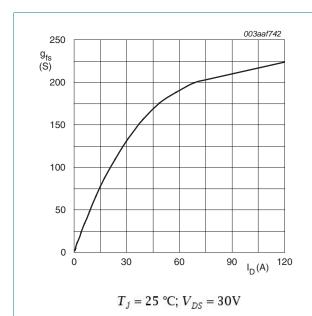


Fig 5. Forward transconductance as a function of drain current; typical values

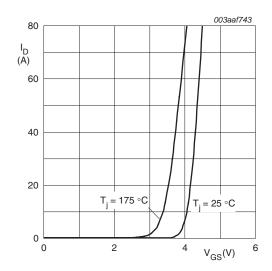


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

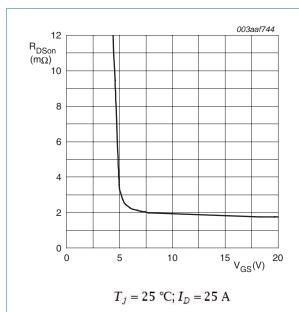


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

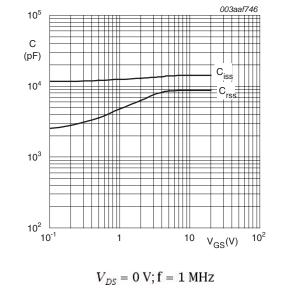


Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

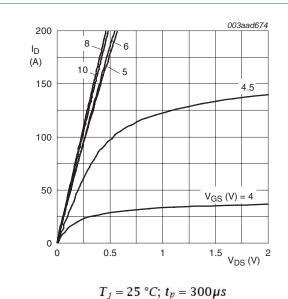
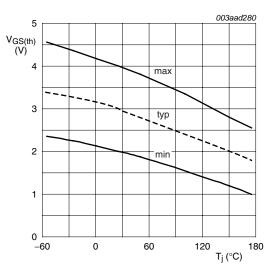


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values



 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

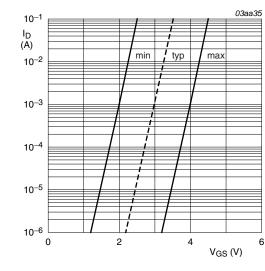
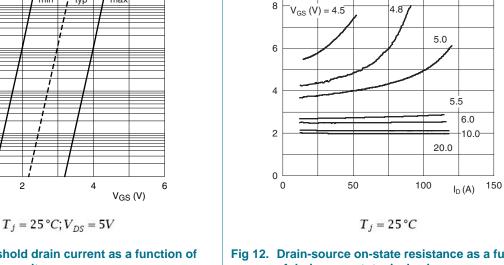


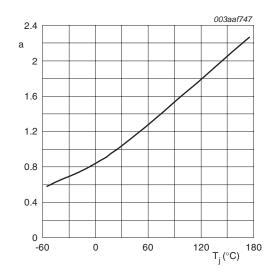
Fig 11. Sub-threshold drain current as a function of gate-source voltage



10 R_{DSon}

 $(m\Omega)$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25$ °C; $I_D = 25$ A

Fig 13. Drain-source on-state resistance as a function of gate-source voltage; typical values

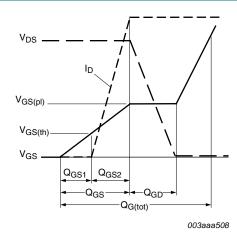


Fig 14. Gate charge waveform definitions

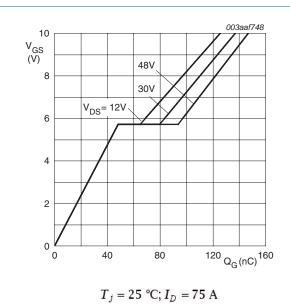
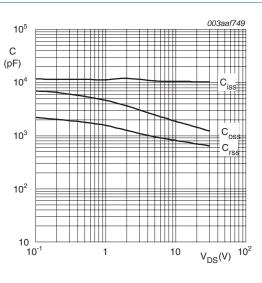
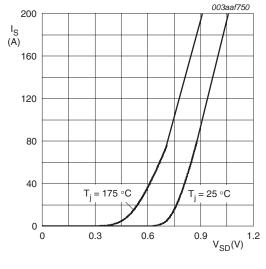


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 \text{ V; } f = 1 \text{ MHz}$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0 \text{ V}$

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

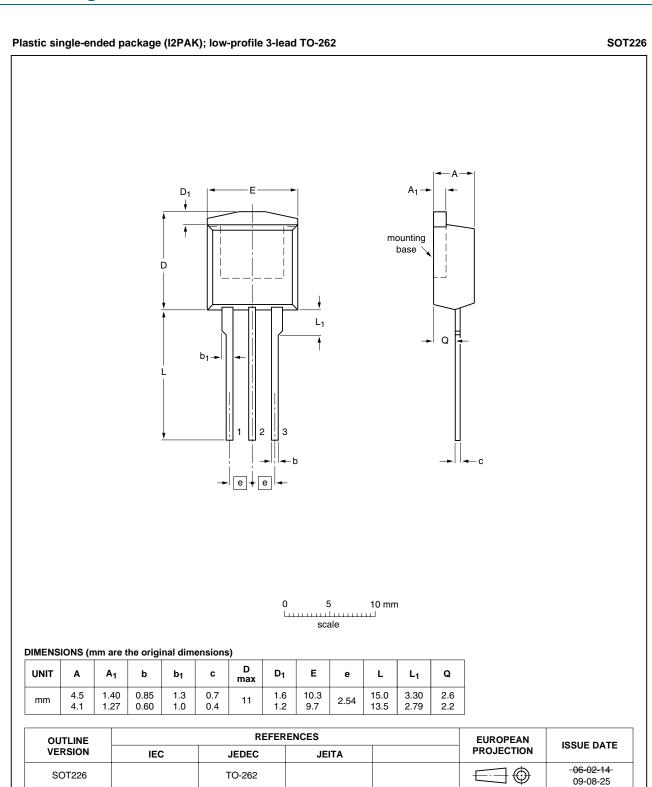


Fig 18. Package outline SOT226 (I2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R0-60ES v.2	20110419	Product data sheet	-	PSMN2R0-60ES v.1
Modifications:	•	from objective to product.		
	 Various changes 	s to content.		
PSMN2R0-60ES v.1	20110117	Objective data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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PSMN2R0-60ES

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PSMN2R0-60ES

N-channel 60 V 2.2 mΩ standard level MOSFET in I2PAK

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PSMN2R0-60ES

Nexperia

N-channel 60 V 2.2 m Ω standard level MOSFET in I2PAK

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